

Fig. 1 PRIOR ART

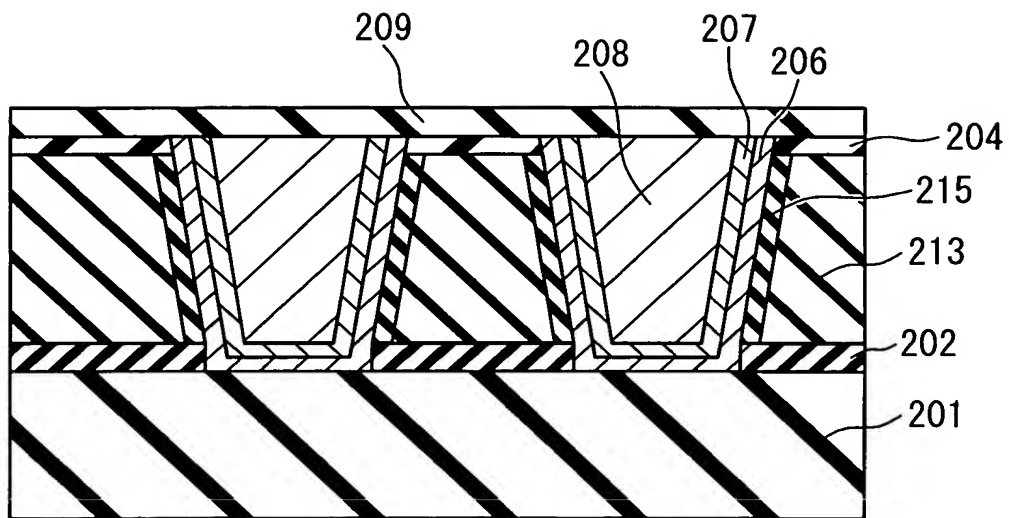


Fig. 2A PRIOR ART

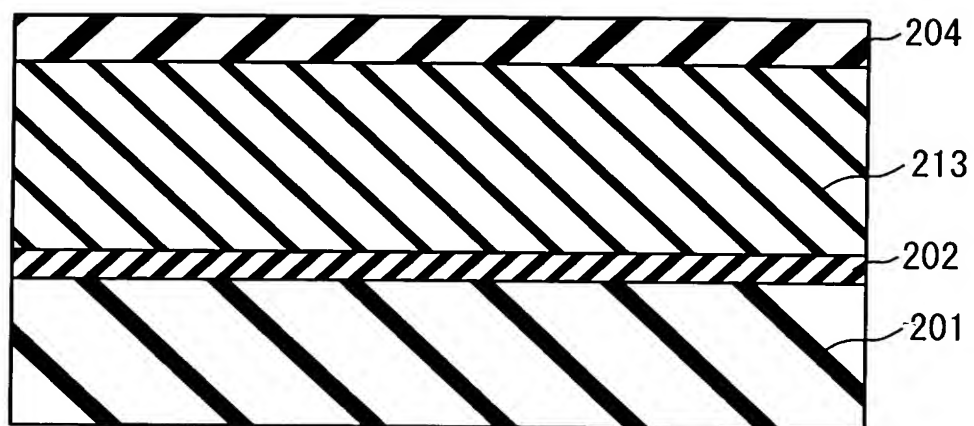
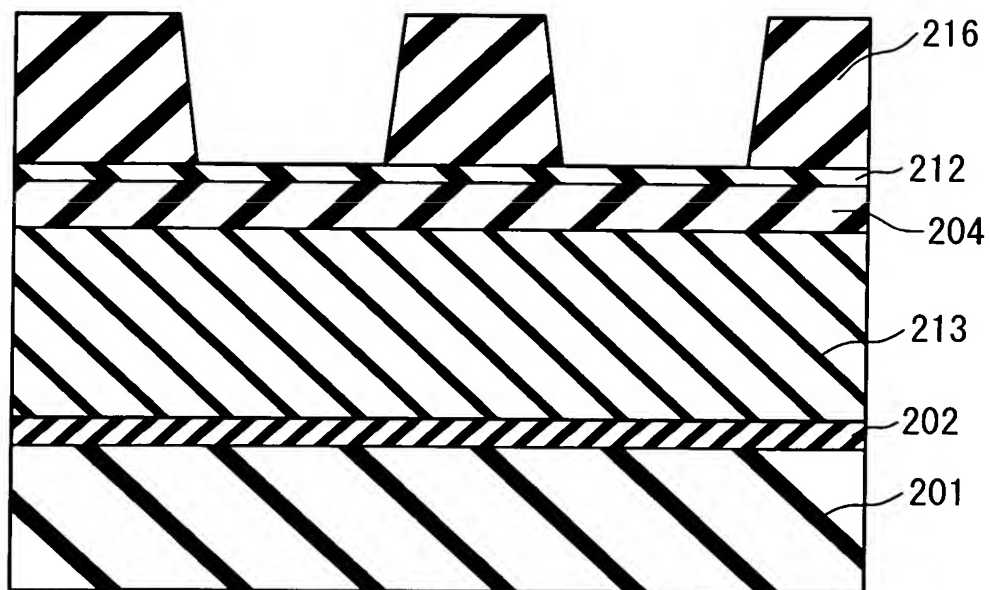


Fig. 2B PRIOR ART



A cross-sectional view of a semiconductor device. It features a base layer 201 with diagonal hatching. On top of this base are three pillars. Each pillar has a bottom layer 202 with diagonal hatching, a middle layer 213 with diagonal hatching, and a top layer 204 with horizontal hatching. The pillars are separated by gaps 220. The side walls of the pillars are labeled 215.

Fig. 3A PRIOR ART

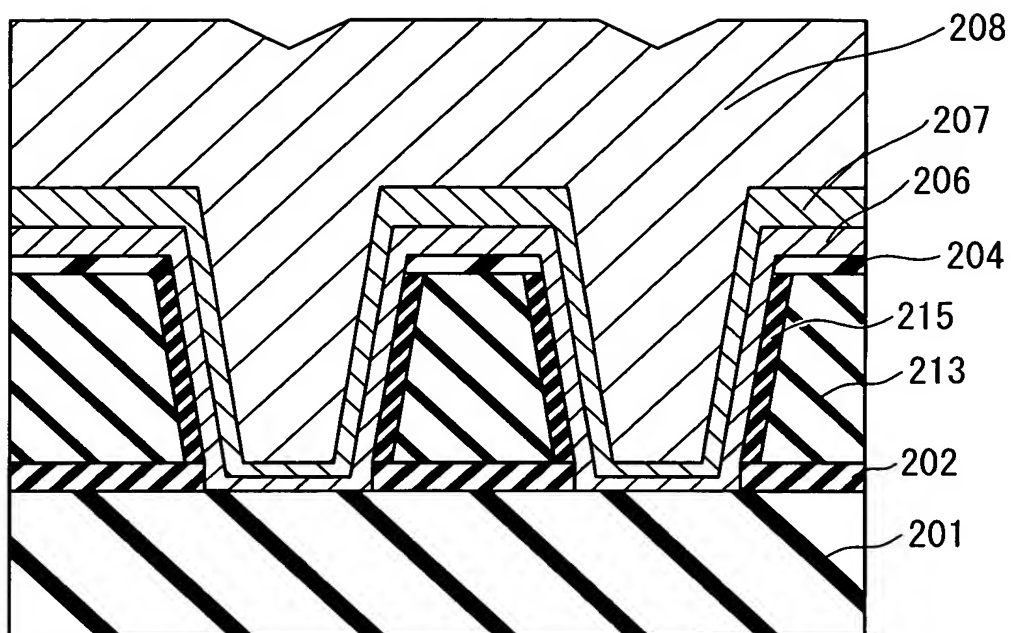


Fig. 3B PRIOR ART

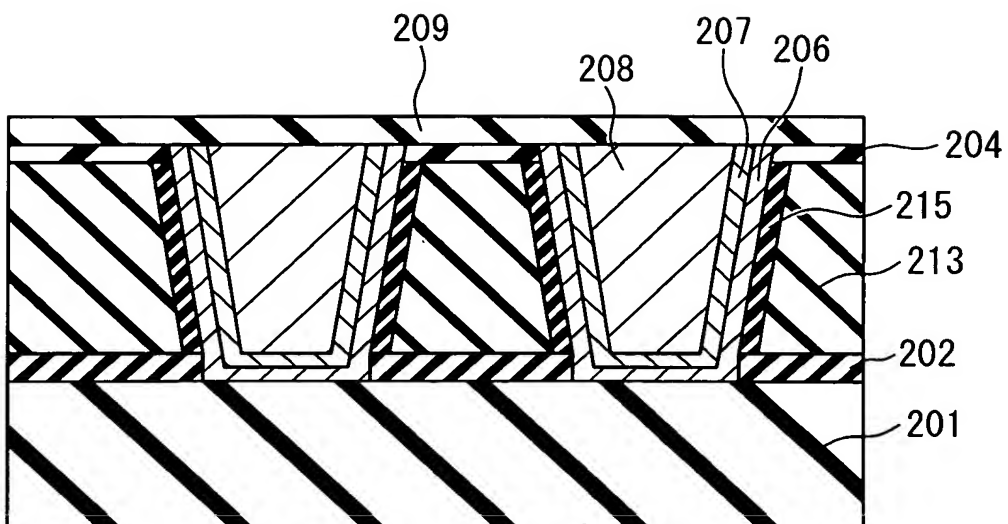


Fig. 4

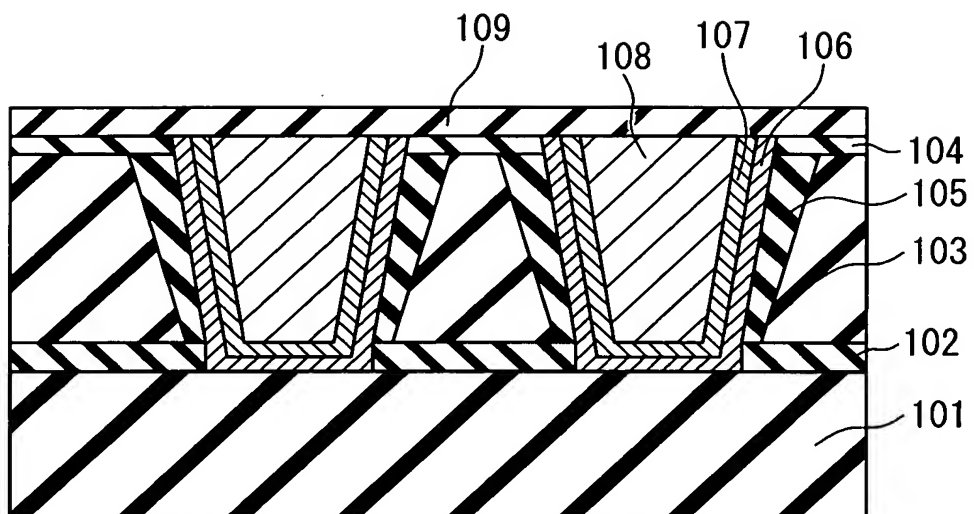


Fig. 5A

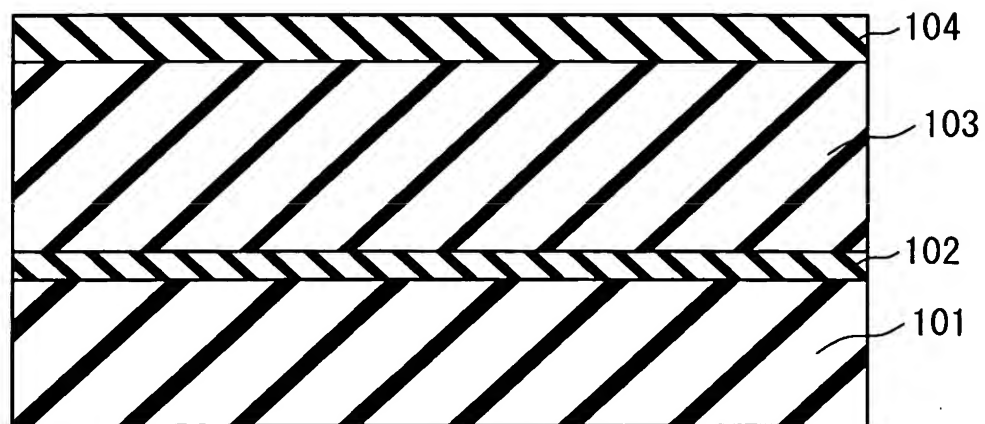


Fig. 5B

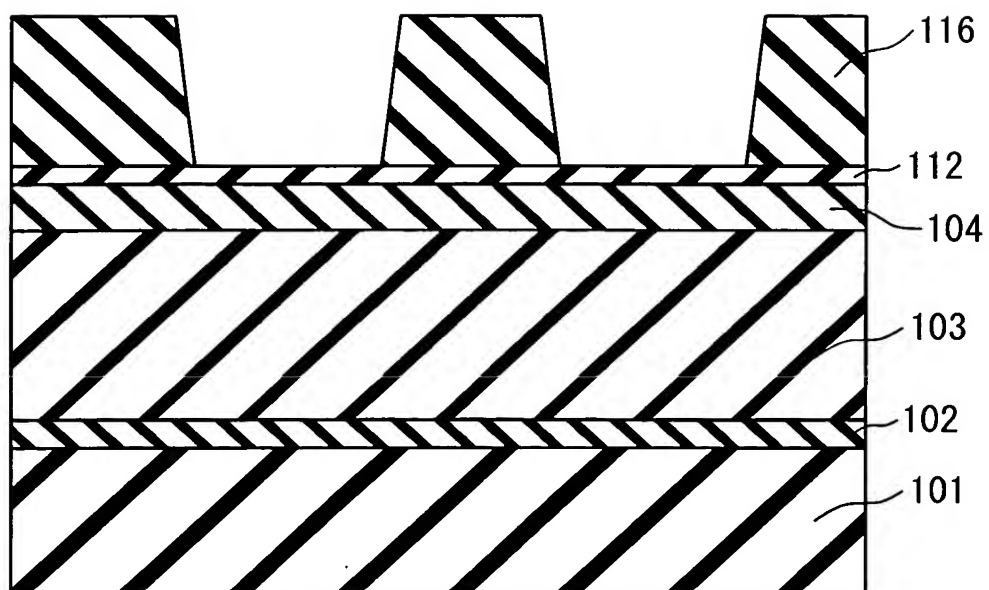


Fig. 5C

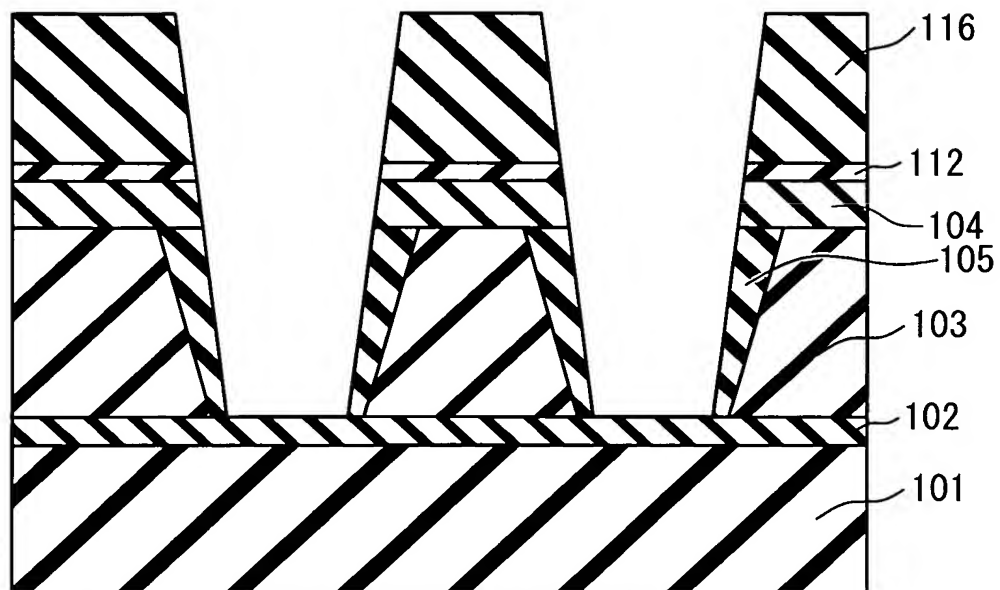


Fig. 5D

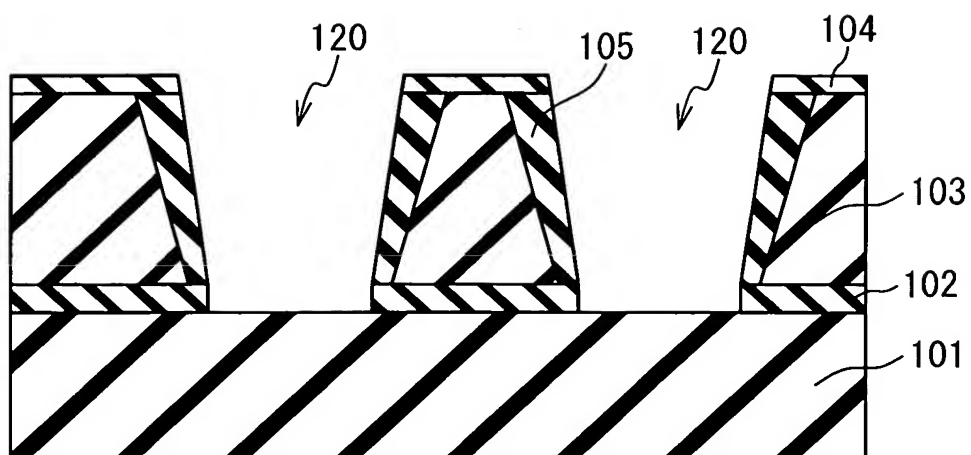


Fig. 6A

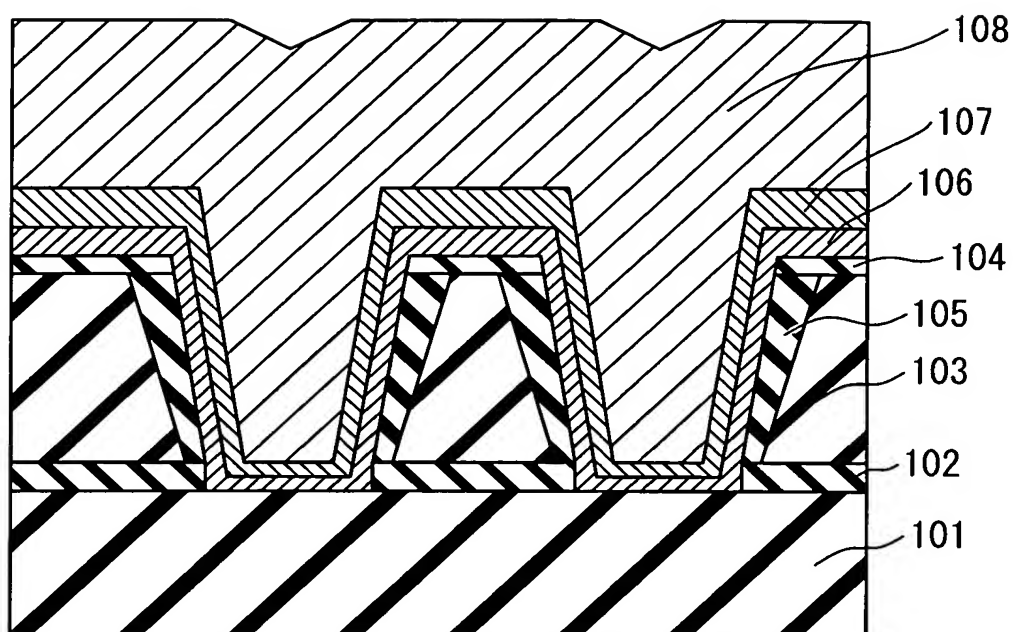


Fig. 6B

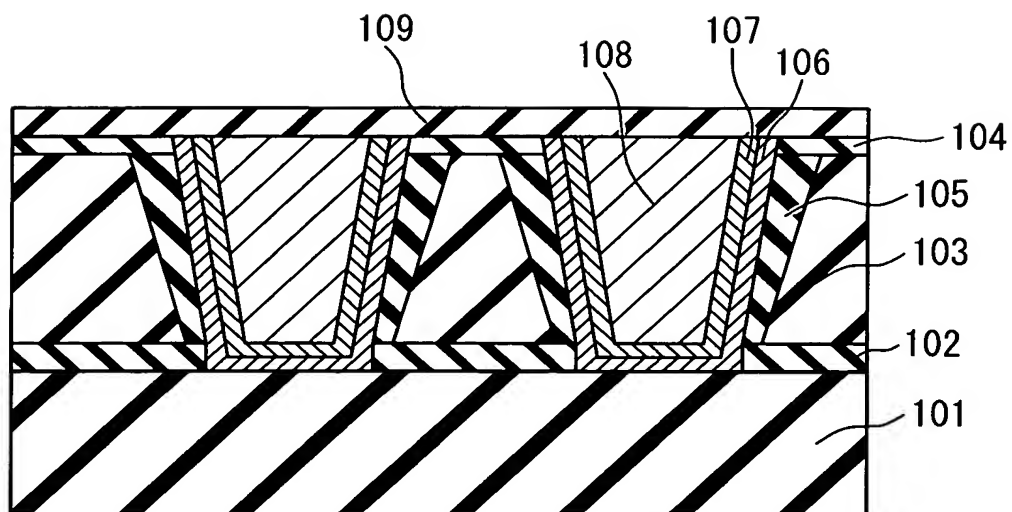




Fig. 7

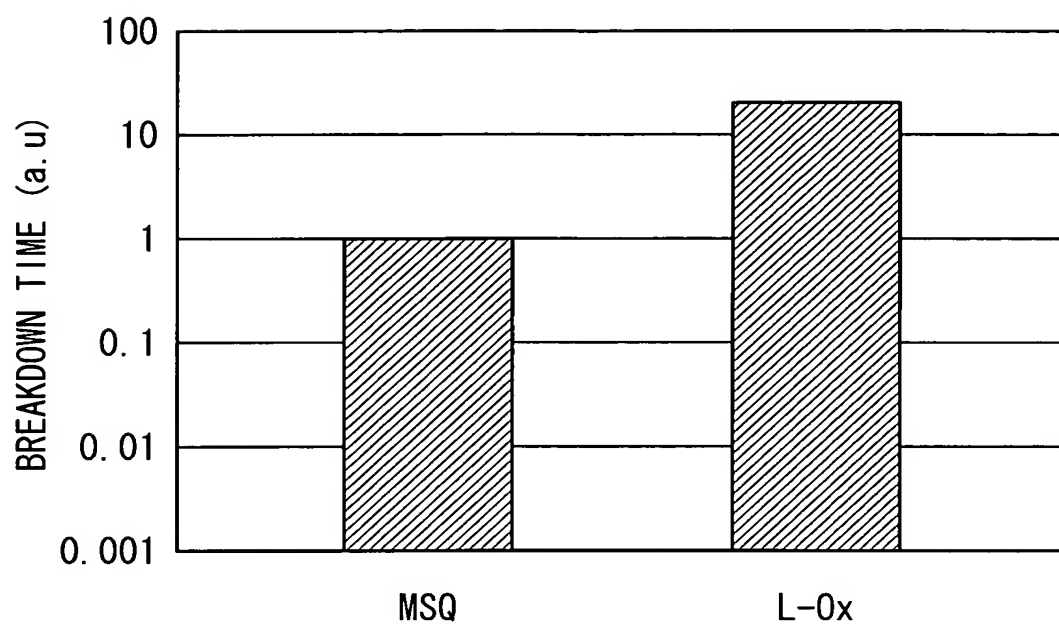


Fig. 8

